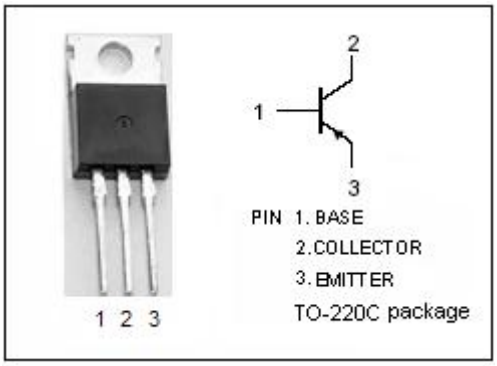
isc Silicon PNP Power Transistor 2SA1355

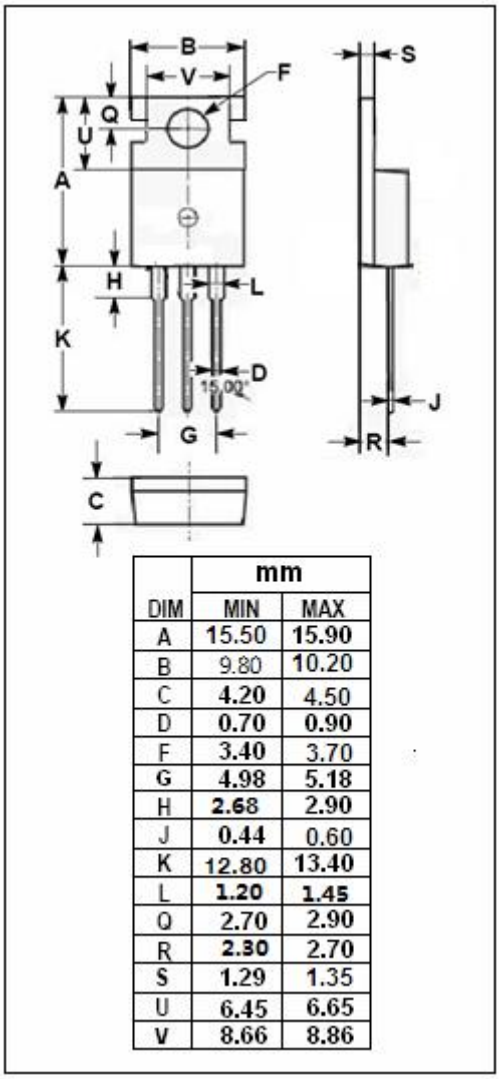


DESCRIPTION

- TO-220 package
- High DC Current Gain
- Low Saturation Voltage
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- This type of power transistor is developed for high-speed switching and features a high h_{FE} at low $V_{CE(sat)}$,which is ideal for use as a driver in DC/DC converters and actuators.



DIM	mm MIN	MAX
A	15.50	15.90
B	9.80	10.20
C	4.20	4.50
D	0.70	0.90
F	3.40	3.70
G	4.98	5.18
H	2.68	2.90
J	0.44	0.60
K	12.80	13.40
L	1.20	1.45
Q	2.70	2.90
R	2.30	2.70
S	1.29	1.35
U	6.45	6.65
V	8.66	8.86

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-70	V
V_{CEO}	Collector-Emitter Voltage	-70	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-4	A
P_T	Total Power Dissipation @T_C=25℃	30	W
	Total Power Dissipation @T_a=25℃	3.0	
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55~150	℃

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ELECTRICAL CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	I_C= -1mA ; R_{BE}= ∞	-70			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -2A; I_B= -0.2A			-0.5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= -2A; I_B= -0.2A			-1.2	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -40V ; I_E=0			-10	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -4V; I_C=0			-10	μA
h_{FE}	DC Current Gain	I_C= -1.0A ; V_{CE}= -2V	70		280	
f_T	Current-Gain—Bandwidth Product	I_C=-1A ; V_{CE}= -5V		40		MHz